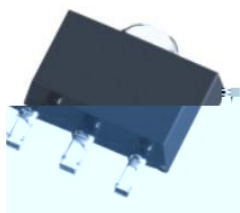
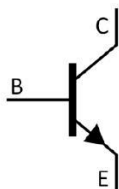


SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

Low $V_{CE(sat)}$, High performance at low supply voltage.

AF Power amplifier.

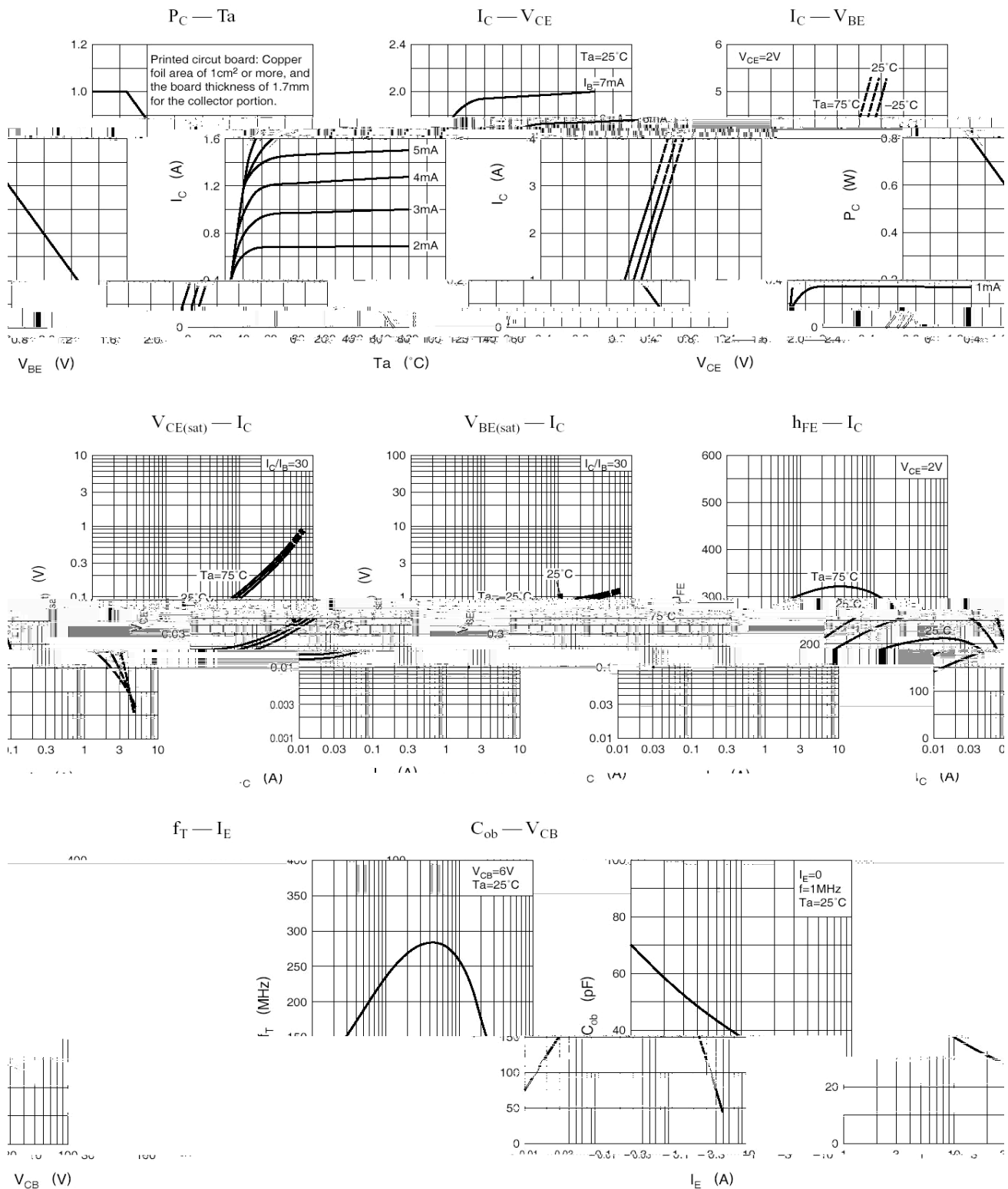


PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	180~270	230~380	340~600
Marking	HTP * *	HTQ * *	HTR * *

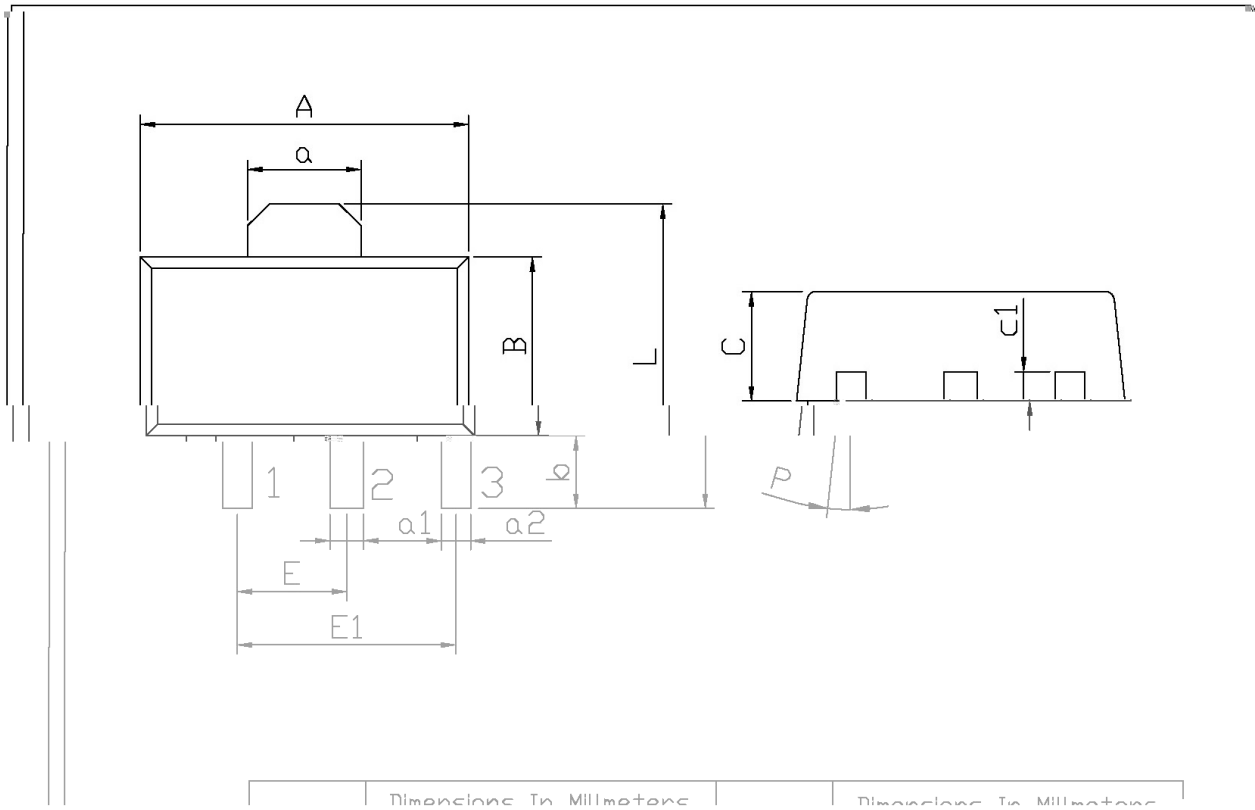
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current-Continuous	I_C	3.0	A
Collector Current -Continuous(Pulse)	I_{CP}	5.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10mA$ $I_C=0$	7.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=10V$ $I_E=0$			0.1	A

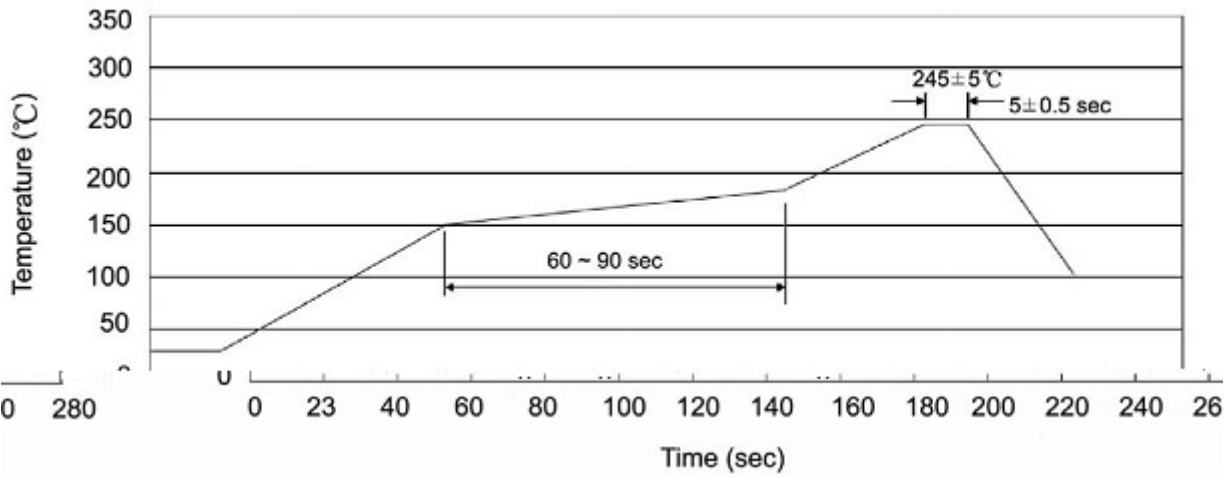


SOT-89

单位: mm



L	3.8/8	4.4/8°	C	1.40	1.70
a	1.45	1.65	c1	0.35	0.50
E	1.40	1.60	P	6°	
E1	2.80	3.20			
b	0.80	1.20			



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						"		